





LOW $V_{CE(SAT)}$ PNP SURFACE MOUNT TRANSISTOR

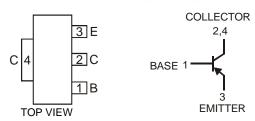
Features

- Epitaxial Planar Die Construction
- Complementary NPN Type Available (DZT651)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

Mechanical Data

- Case: SOT-223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish Matte Tin annealed over Copper Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking & Type Code Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.115 grams





Schematic and Pin Configuration

Maximum Ratings @T_A = 25°C unless otherwise specified

| Characteristic | Symbol | Value | Unit |
|------------------------------|------------------|-------|------|
| Collector-Base Voltage | V _{CBO} | -80 | V |
| Collector-Emitter Voltage | V _{CEO} | -60 | V |
| Emitter-Base Voltage | V _{EBO} | -5 | V |
| Continuous Collector Current | Ic | -3 | A |
| Peak Pulse Collector Current | Ісм | -6 | А |

Thermal Characteristics

| Characteristic | Symbol | Value | Unit |
|---|-----------------------------------|--------------------------|------|
| Power Dissipation @ T _A = 25°C | P_{D} | 1 (Note 3) 2 (Note 4) | W |
| Thermal Resistance, Junction to Ambient Air (Note 3) @T _A = 25°C | $R_{	heta JA}$ | 125 | °C/W |
| Operating and Storage Temperature Range | T _j , T _{STG} | -55 to +150 | °C |

Notes:

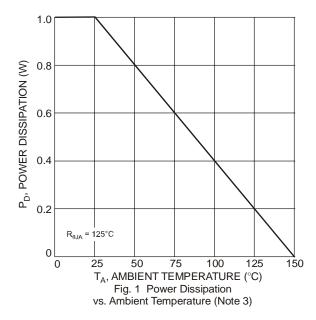
- 1. No purposefully added lead.
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- Device mounted on FR-4 PCB, pad layout as shown on last page or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf, or on page 4 of this data sheet.
- 4. Device mounted on Polyimide PCB with 1.8cm² copper area.

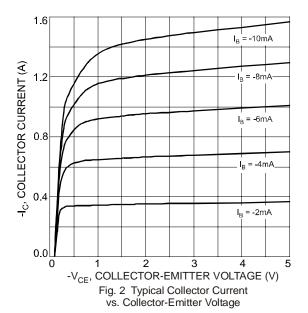


Electrical Characteristics @T_A = 25°C unless otherwise specified

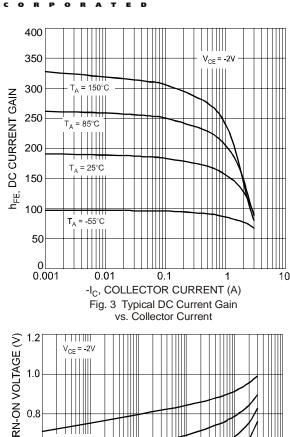
| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition |
|--------------------------------------|-------------------------------------|-----------------------|--------------------------|---------------|--------------------------|---|
| OFF CHARACTERISTICS (Note 5) | | | | | | |
| Collector-Base Breakdown Voltage | V _{(BR)CBO} | -80 | _ | _ | V | $I_C = -100 \mu A, I_E = 0$ |
| Collector-Emitter Breakdown Voltage | V _{(BR)CEO} | -60 | _ | | V | $I_C = -10 \text{mA}, I_B = 0$ |
| Emitter-Base Breakdown Voltage | V _{(BR)EBO} | -5 | | | V | $I_E = -100 \mu A, I_C = 0$ |
| Collector Cutoff Current | I _{CBO} | _ | | -0.1 -10 | μ Α μ Α | $V_{CB} = -60V, I_{E} = 0$ $V_{CB} = -60V, I_{E} = 0, T_{A} = 100^{\circ}C$ |
| Emitter Cutoff Current | I _{EBO} | _ | _ | -0.1 | μΑ | $V_{EB} = -4V, I_{C} = 0$ |
| ON CHARACTERISTICS (Note 5) | | | | | | |
| Collector-Emitter Saturation Voltage | V _{CE(SAT)} | _ | -0.08 | -0.3 | V | $I_C = -1A$, $I_B = -100mA$ |
| | | | -0.2 | -0.6 | V | $I_C = -3A$, $I_B = -300mA$ |
| Base-Emitter Saturation Voltage | $V_{BE(SAT)}$ | _ | -0.9 | -1.25 | V | $I_C = -1A$, $I_B = -100mA$ |
| Base-Emitter Turn-On Voltage | V _{BE(ON)} | | -0.8 | -1 | V | $V_{CE} = -2V, I_{C} = -1A$ |
| DC Current Gain | h _{FE} | 70 100 80 40 | 200 180 160 140 | 300 — — | _ | $V_{CE} = -2V, I_{C} = -50 \text{mA}$ $V_{CE} = -2V, I_{C} = -500 \text{mA}$ $V_{CE} = -2V, I_{C} = -1 \text{A}$ $V_{CE} = -2V, I_{C} = -2 \text{A}$ |
| AC CHARACTERISTICS | | | | | | |
| Transition Frequency | f⊤ | 100 | 145 | | MHz | $V_{CE} = -5V, I_{C} = -100mA,$ f = 100MHz |
| Output Capacitance | C _{obo} | _ | | 30 | pF | $V_{CB} = -10V$, $f = 1MHz$ |
| Switching Times | t _{on} t _{off} | _ | 45 200 | | ns ns | $V_{CC} = -10V$, $I_{C} = -500$ mA, $I_{B1} = I_{B2} = -50$ mA |

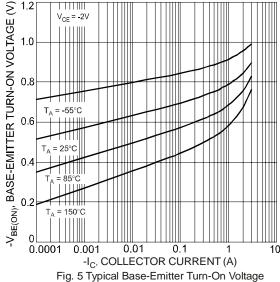
Notes: 5. Pulse Test: Pulse width $\leq 300 \mu s$. Duty cycle $\leq 2.0\%$.

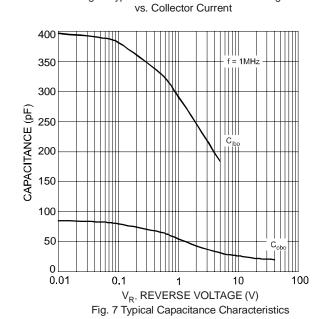












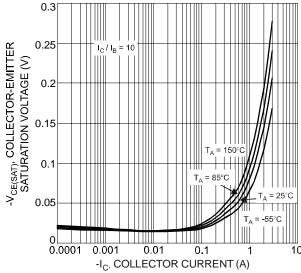


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

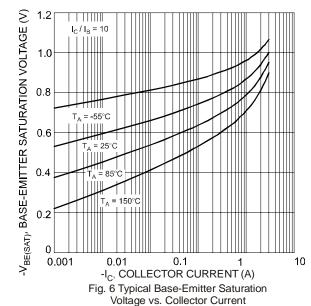


Fig. 8 Typical Gain-Bandwidth Product vs. Collector Current

20 30 40 50 60 70 80 -I_C, COLLECTOR CURRENT (mA)

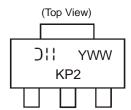


Ordering Information (Note 6)

| Device | | Packaging | Shipping | |
|--------|-----------|-----------|------------------|--|
| | DZT751-13 | SOT-223 | 2500/Tape & Reel | |

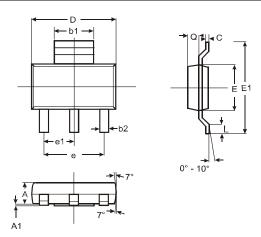
Notes: 6. For packaging details, please go to our website at http://www.diodes.com/ap02007.pdf.

Marking Information



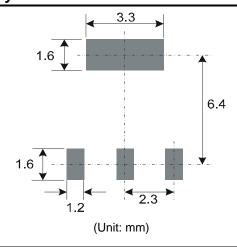
KP2 = Product Type Marking Code YWW = Date Code Marking Y = Last digit of year ex: 7 = 2007 WW = Week code 01 - 52

Package Outline Dimensions



| SOT-223 | | | | | | |
|----------------------|-------|------|------|--|--|--|
| Dim | Min | Max | Тур | | | |
| Α | 1.55 | 1.65 | 1.60 | | | |
| A1 | 0.010 | 0.15 | 0.05 | | | |
| b1 | 2.90 | 3.10 | 3.00 | | | |
| b2 | 0.60 | 0.80 | 0.70 | | | |
| С | 0.20 | 0.30 | 0.25 | | | |
| D | 6.45 | 6.55 | 6.50 | | | |
| Е | 3.45 | 3.55 | 3.50 | | | |
| E1 | 6.90 | 7.10 | 7.00 | | | |
| е | _ | _ | 4.60 | | | |
| e1 | _ | _ | 2.30 | | | |
| L | 0.85 | 1.05 | 0.95 | | | |
| Ø | 0.84 | 0.94 | 0.89 | | | |
| All Dimensions in mm | | | | | | |

Suggested Pad Layout



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